

CPW4-1200S015B–silicon Carbide Schottky Diode Chip

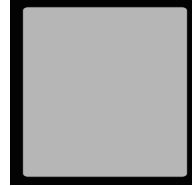
Z-REC™ RECTIFIER

V_{RRM}	= 1200 V
I_F	= 15 A
Q_c	= 96 nC

Features

- 1200-Volt Schottky Rectifier
- Zero Reverse Recovery
- Zero Forward Recovery
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

Chip Outline



Part Number	Anode	Cathode	Package	Marking
CPW4-1200S015B	Al	Ni/Ag	Sawn on Foil	Wafer # on Foil

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_{DC}	DC Blocking Voltage	1200	V		
$I_{F(AVG)}$	Average Forward Current	15	A	$T_J=175^\circ\text{C}$	
I_{FRM}	Repetitive Peak Forward Surge Current	68	A	$T_C=25^\circ\text{C}$, $t_p=10$ ms, Half Sine pulse	1
I_{FSM}	Non-Repetitive Peak Forward Surge Current	130	A	$T_C=25^\circ\text{C}$, $t_p=10$ ms, Half Sine pulse	1
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		



Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.6 2.3	1.8 3	V	$I_F = 15\text{ A}$ $T_J = 25^\circ\text{C}$ $I_F = 15\text{ A}$ $T_J = 175^\circ\text{C}$	
I_R	Reverse Current	35 120	200 300	μA	$V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$	
Q_C	Total Capacitive Charge	96		nC	$V_R = 1200\text{ V}$, $I_F = 15\text{ A}$ $di/dt = 200\text{ A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$	
C	Total Capacitance	1200 70 50		pF	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 400\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$ $V_R = 800\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	

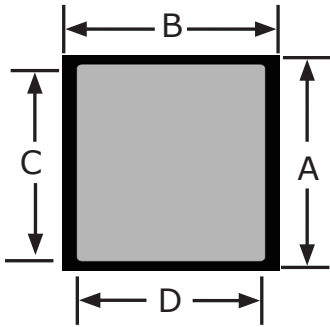
Note:

- Assumes θ_{JC} Thermal Resistance of $0.78^\circ\text{C}/\text{W}$ or less

Mechanical Parameters

Parameter	Typ.	Unit
Die Size	2.70 x 2.70	mm
Anode Pad Size	2.42 x 2.42	mm
Anode Pad Opening	2.14 x 2.14	mm
Thickness	377 \pm 10%	μm
Wafer Size	100	mm
Anode Metalization (Al)	4	μm
Cathode Metalization (Ni/Ag)	1.8	μm
Frontside Passivation	Polyimide	

Chip Dimensions



symbol	dimension	
	mm	inch
A	2.7	0.106
B	2.7	0.106
C	2.14	0.084
D	2.14	0.084

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The die-on-tape method of delivering these SiC die may be considered a means of temporary storage only. Due to an increase in adhesion over time, die stored for an extended period may affix too strongly to the tape. These die should be stored in a temperature-controlled nitrogen dry box soon after receipt. Cree will further recommend that all die be removed from tape to a waffle pack, to a similar storage medium, or used in production within 2 – 3 weeks of delivery to assure 100% release of all die without issues.